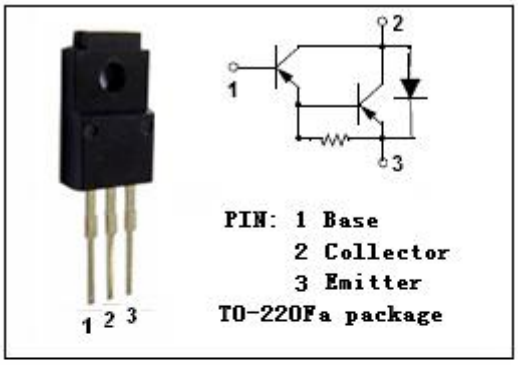
isc Silicon PNP Darlington Power Transistor 2SB950A



DESCRIPTION

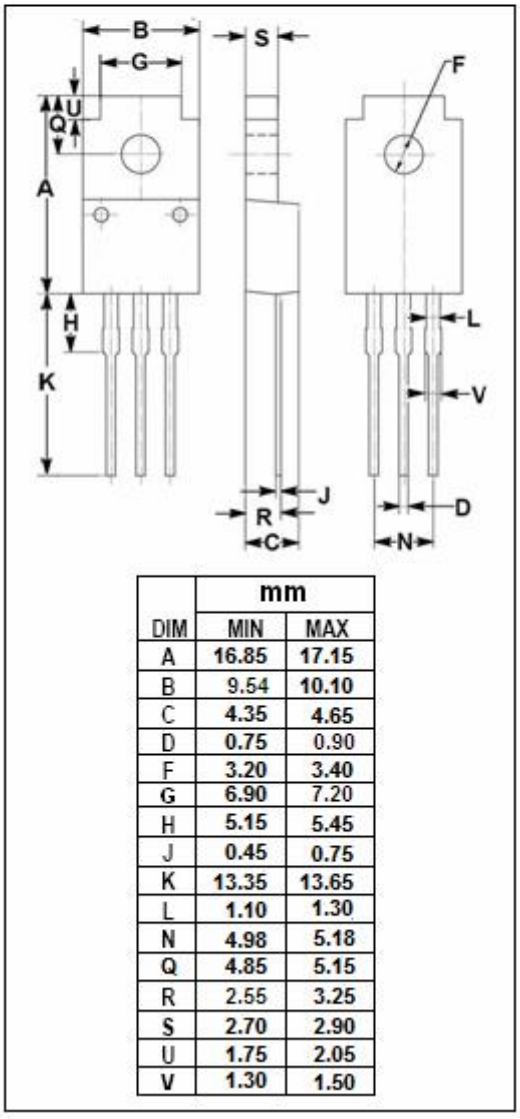
- High DC Current Gain-
  : h_{FE}= 2000(Min.)@I_C= -3A
- High Speed Switching
- Complement to Type 2SD1276A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for power amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-4	A
I_{CM}	Collector Current-Peak	-8	A
P_C	Collector Power Dissipation @ T_a=25℃	2	W
	Collector Power Dissipation @ T_C=25℃	40	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	16.85	17.15
B	9.54	10.10
C	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
H	5.15	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -30mA ; I_B= 0	-80			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -12mA			-2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -5A; I_B= -20mA			-4.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -3A ; V_{CE}= -3V			-2.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V ; I_E= 0			-0.2	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= -40V ; I_B= 0			-0.5	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V ; I_C= 0			-2.0	mA
h_{FE-1}	DC Current Gain	I_C= -0.5A ;V_{CE}= -3V	1000			
h_{FE-2}	DC Current Gain	I_C= -3A ; V_{CE}= -3V	2000		10000	

◆ **h_{FE-2} Classifications**

Q	P
2000-5000	4000-10000